AMENDMENTS TO THE SPECIFICATION

Please **revise the paragraph beginning at page 2, line 12 of the specification** as follows:

In order to solve such impediment, Japan Laid-Open Patent Publication (JP-A) No. 2002-134729 describes a MOS type solid-state imaging device that comprises an overflow drain region with a conductive type (n-type for instance) opposite to the charge generating region and the carrier pocket (p-type for instance). The overflow drain region serves as the potential ~~burrier~~ barrier to the photo-generated charges. For the purpose of removing the photo-generated charges to the substrate, transfer gate electrodes are formed on the overflow drain region to control the potential ~~burrier~~ barrier. Therefore, it is possible to start/finish to accumulate the photo-generated charges of whole pixels at the same time. That is, controlling the potential ~~burrier~~ barrier works as a global electrical shutter.